

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended) A deposition method comprising the steps of:
providing a substrate comprising an active substrate comprising at least one material selected from the group consisting of a metal, metal alloy, and metal containing compound;
contacting the substrate with an a non-aqueous organic solution comprising a desired deposition galvanic coating component, the desired deposition galvanic coating component having a more noble composition than the less noble composition of the active substrate; and
spontaneously displacing the active substrate with [[a]] the desired deposition galvanic coating component; and
~~spontaneously depositing the desired deposition component from the organic solution onto the active substrate.~~
2. (cancelled)
3. (currently amended) The method of claim 1 wherein the ~~deposited or displacing~~ desired deposition component ~~further~~ comprises a seed composition comprising a material selected from the group consisting of copper, platinum, palladium, gold, zinc, iron, cadmium, silver, lead, cobalt, nickel, and mixtures thereof.
4. (currently amended) The method of claim 1 wherein the desired deposition component comprises ~~at least one material selected from the group consisting of a metal, a metal alloy, a metal compound, a metal ion, and an organometallic complex.~~
5. (currently amended) The method of claim 4 wherein the desired deposition component comprises a material selected from the group consisting of copper, gold, platinum, palladium, silver, lead, zinc, tin, nickel, iron, and mixtures thereof.
6. (cancelled)
7. (cancelled)
8. (cancelled)

9. (previously presented) The method of claim 1 wherein the substrate comprises at least one material selected from the group consisting of tungsten-based, tantalum-based, and titanium-based materials.

10. (previously presented) The method of claim 9 wherein said substrate comprises at least one material selected from the group consisting of Ti, Ta, W, TiN, TaN, W₂N, TiSiN, WN, WSiN and TaSiN.

11. (previously presented) The method of claim 1 wherein the active substrate comprises at least one material selected from the group consisting of copper, nickel, iron, aluminum, steel, zinc and silver.

12. (cancelled)

13. (previously presented) The method of claim 1 wherein the organic solution comprises at least two deposition components.

14. (previously presented) The method of claim 1 wherein the substrate comprises a barrier layer.

15. (previously presented) The method of claim 1 further comprising the step of treating the substrate.

16. (previously presented) The method of claim 15 wherein the treating step comprises introducing a halogenated compound into the organic solution.

17. (previously presented) The method of claim 16 wherein the halogenated compound comprises at least one material selected from the group consisting of HBF₄, HF, NaF, H₂SiF₆, and HCl.

18. (previously presented) The method of claim 15 wherein the treating step comprises introducing a non-halogenated compound into the organic solution.

19. (original) The method of claim 18 wherein the non-halogenated compound comprises H₂SO₄.

20. (cancelled)

21. (cancelled)
22. (cancelled)
23. (cancelled)
24. (cancelled)
25. (cancelled)
26. (cancelled)
27. (previously presented) The method of claim 1 wherein the organic solution comprises a cation exchange reactant.
28. (cancelled)
29. (cancelled)
30. (cancelled)
31. (cancelled)
32. (cancelled)
33. (cancelled)
34. (cancelled)
35. (cancelled)
36. (cancelled)
37. (cancelled)
38. (cancelled)

- 39. (cancelled)
- 40. (cancelled)
- 41. (cancelled)
- 42. (cancelled)
- 43. (cancelled)
- 44. (Original) The method of claim 1 further comprising the step of using temperatures from ambient to elevated levels.
- 45. (cancelled)
- 46. (cancelled)
- 47. (cancelled)
- 48. (previously presented) The method of claim 1 wherein the organic solution comprises less than 5% water by volume.
- 49. (currently amended) The method of claim 1 wherein the organic solution comprises most preferably less than 0.25% water by volume.
- 50. (previously presented) The method of claim 1 further comprising removing a barrier layer.
- 51. (previously presented) The deposition method of claim 1 wherein the depositing of the desired deposition component comprises displacing components from a layer of the active substrate with the desired deposition component.
- 52. (cancelled)
- 53. (new) The method of claim 14 wherein the barrier layer comprises at least one material selected from the group consisting of a metal nitride, a metal silicate, a metal combination and a non-metal combination.

54. (new) The method of claim 1 wherein galvanic coating comprises simultaneous galvanic coating comprising:

reacting a loaded organic solution, a metal, and an aqueous stripping phase;
settling; and
separating said metal and stripping phase.

55. (new) The method of claim 1 wherein galvanic coating comprises separate galvanic coating comprising:

loading the organic solution with the deposition component; and
reactively reducing in the organic solution.

56. (new) The method of claim 1 wherein the desired deposition component comprises a metal alloy.

57. (new) The method of claim 1 wherein the desired deposition component comprises a metal compound.

58. (new) The method of claim 1 wherein the desired deposition component comprises a metal ion.

59. (new) The method of claim 1 wherein the desired deposition component comprises an organometallic complex.